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"Si")) and (spin\$4 or spun or rotat\$3 or turn\$3) same (exhaust\$3 or air or sweep\$3 or swept or inert or gas\$4)) and (resist or photoresist or photopolym\$7) same (prim\$3 or pre adj treat\$3 or pretreat\$3) (((resist or photoresist or photopolymer\$7) and (semiconduct\$3 or photopolymer\$7) and (semiconduct\$3 or silicon or "Si" or wafer or substrate) same (HMDS or hexamethyldisilazane or hexamethyl adj disilazane) same (prim\$3 or pretreat\$4 or pre adj treat\$4)) not ((semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyl adj disilazane or silazane) same prim\$3)) and (((HMDS or hexamethyldisilazane or					
turn\$3) same (exhaust\$3 or air or sweep\$3 or swept or inert or gas\$4)) and (resist or photoresist or photopolym\$7) same (prim\$3 or pre adj treat\$3 or pretreat\$3) (((resist or photoresist or photopolymer\$7) and (semiconduct\$3 or same (HMDS or hexamethyldisilazane or pretreat\$4 or pre adj treat\$4)) not ((semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyl adj disilazane) same prim\$3)) and (((HMDS or hexamethyldisilazane or			i '		
or swept or inert or gas\$4)) and (resist or photoresist or photopolym\$7) same (prim\$3 or pre adj treat\$3 or pretreat\$3) (((resist or photoresist or photopolymer\$7) and (semiconduct\$3 or silicon or "Si" or wafer or substrate) same (HMDS or hexamethyldisilazane or pretreat\$4 or pre adj treat\$4)) not ((semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyl adj disilazane or silazane) same prim\$3)) and (((HMDS or hexamethyldisilazane or			"Si")) and (spin\$4 or spun or rotat\$3 or		
or photoresist or photopolym\$7) same (prim\$3 or pre adj treat\$3 or pretreat\$3) (((resist or photoresist or photopolymer\$7) and (semiconduct\$3 or silicon or "Si" or wafer or substrate) same (HMDS or hexamethyldisilazane or hexamethyl adj disilazane) same (prim\$3 or pretreat\$4 or pre adj treat\$4)) not ((semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3)) and (((HMDS or hexamethyldisilazane or					
(prim\$3 or pre adj treat\$3 or pretreat\$3) (((resist or photoresist or photopolymer\$7) and (semiconduct\$3 or silicon or "Si" or wafer or substrate) same (HMDS or hexamethyldisilazane or hexamethyl adj disilazane) same (prim\$3 or pretreat\$4 or pre adj treat\$4)) not ((semiconduct\$3 same (defect\$3 and (resist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyl adj disilazane or silazane) same prim\$3)) and (((HMDS or hexamethyldisilazane or					
7 97 (((resist or photoresist or photopolymer\$7) and (semiconduct\$3 or silicon or "Si" or wafer or substrate) same (HMDS or hexamethyldisilazane or hexamethyl adj disilazane) same (prim\$3 or pretreat\$4 or pre adj treat\$4)) not ((semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3)) and (((HMDS or hexamethyldisilazane or					
photopolymer\$7) and (semiconduct\$3 or silicon or "Si" or wafer or substrate) same (HMDS or hexamethyldisilazane or hexamethyl adj disilazane) same (prim\$3 or pretreat\$4 or pre adj treat\$4)) not ((semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3)) and (((HMDS or hexamethyldisilazane or					
silicon or "Si" or wafer or substrate) same (HMDS or hexamethyldisilazane or hexamethyl adj disilazane) same (prim\$3 or pretreat\$4 or pre adj treat\$4)) not ((semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3)) and (((HMDS or hexamethyldisilazane or	7	97			2004/01/08 19:53
same (HMDS or hexamethyldisilazane or hexamethyl adj disilazane) same (prim\$3 or pretreat\$4 or pre adj treat\$4)) not ((semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3)) and (((HMDS or hexamethyldisilazane or					
hexamethyl adj disilazane) same (prim\$3 or pretreat\$4 or pre adj treat\$4)) not ((semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3)) and (((HMDS or hexamethyldisilazane or				EPO; JPO;	
pretreat\$4 or pre adj treat\$4)) not ((semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3)) and (((HMDS or hexamethyldisilazane or			· •	IBM_TDB	
((semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3)) and (((HMDS or hexamethyldisilazane or					
or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3)) and (((HMDS or hexamethyldisilazane or	,				
develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3)) and (((HMDS or hexamethyldisilazane or					
hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3)) and (((HMDS or hexamethyldisilazane or					
disilazane or silazane) same prim\$3)) and (((HMDS or hexamethyldisilazane or					
(((HMDS or hexamethyldisilazane or					
hexamethyl adj disilazane or silazane) or					
prim\$3) near5 vapor) same (seconds or	l		(-		-
"sec")	L		"sec")		

8	157	(430/311,326-327,329.ccls. and (((resist or photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not ((((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3)) and (semiconduct\$3 or wafer or silicon or "Si")) and (spin\$4 or spun or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas\$4)) and (resist or photoresist or photopolym\$7) same (prim\$3 or pre adj treat\$3 or pretreat\$3)))) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (revolution or "rpm")	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/01/08 20:05
9	11	(semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/01/08 20:11
10	13	(((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/01/08 20:16
11	4	(("6613500") or ("6486072") or ("6222936") or ("5985497")).PN.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/01/08 20:34
_	226	semiconduct\$3 and HMDS with prim\$3	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/19 18:13
-	2005	semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 08:26
_	10	(semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3 (semiconduct\$3 or silicon or "Si" or	USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT;	2004/01/08 17:22
	6246	<pre>wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)</pre>	US-PGPUB; EPO; JPO; IBM_TDB	2003/00/20 03.03

		· · · · · · · · · · · · · · · · · · ·
<pre>wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist</pre>	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 09:21
rins\$3) same (spin\$4 or rotat\$3 or turn\$3 or speed\$3)		
wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3 or speed\$3)) and ((develop\$4 or rins\$3) or (spin\$4 or rotat\$3 or turn\$3 or speed\$3)) same (exhaust\$3 or air) near5 (velocit\$3	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 09:10
((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 09:22
(((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/01/08 17:31
((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or dry\$3) same (spin\$4	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 09:21
((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or dry\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 09:22
	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/10/15 15:31
	(resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3 or speed\$3) (((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) and evelop\$4)) and (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3 or speed\$3)) and ((develop\$4 or rins\$3) same (exhaust\$3 or air) near5 (velocit\$3 or speed\$3)) ((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photopolymer\$7) and develop\$4)) and (resist or photopolymer\$7) and develop\$4)) and (resist or photopolymer\$7) and develop\$4)) and (resist or photopolymer\$7) and develop\$4)) and (resist or photopolymer\$7) and develop\$4 or rins\$3 or speed\$3) (wellop\$4 or rins\$3 or speed\$3) and (develop\$4 or rins\$3 or spin\$4 or rotat\$3 or turn\$3) near\$ (velocit\$3 or speed\$3) and (develop\$4 or rins\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near\$ (velocit\$3 or speed\$3) ((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) and develop\$4) and (resist or photopolymer\$7) and develop\$4 or rins\$3 or clean\$3 or turn\$3) near\$ (velocit\$	wafer) same ((defect\$3 or residue) and (resist or photopersist or photopolymer\$7) and develop\$4) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3 or speed\$3) (((semiconduct\$3 or silicon or "\$i" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4) and (resist or photoresist or photopolymer\$7) asme (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3 or speed\$3) ((semiconduct\$3 or silicon or "\$i" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4) and (resist or photoresist or photopolymer\$7) and develop\$4) and (resist or photopolymer\$7) and (resist or photopolymer\$7) and (resist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3) (((semiconduct\$3 or silicon or "\$i" or wafer) same (defect\$3 or residue) and (resist or photopolymer\$7) and (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) same (spin\$4 or rotat\$3 or turn\$3 or speed\$3) ((semiconduct\$3 or silicon or "\$i" or wafer) same ((defect\$3 or residue) and (resist or photopolymer\$7) and develop\$4) and (resist or photopolymer\$7) and (resist or photopolymer\$7) same (develop\$4 or rin\$3 or clean\$3 or dry\$3) same (spin\$4 or rotat\$3 or turn\$3) same (spin\$4 or rotat\$3

	1001	((resist or photoresist or photopolymer\$7)	USPAT;	2003/06/20 17:12
-	1091	same (develop\$4 or rins\$3 or clean\$3 or	US-PGPUB;	
		remov\$3 or residue or rubbish or debris)	EPO; JPO;	
		same (spin\$4 or spun or rotat\$3 or turn\$3)	IBM TDB	
		same (spins4 of spun of folders of curitys)		
		near5 (velocit\$3 or speed\$3)) not		
		((((semiconduct\$3 or silicon or "Si" or		
		wafer) same ((defect\$3 or residue) and		
		(resist or photoresist or photopolymer\$7)		
		and develop\$4)) and (resist or photoresist		
		or photopolymer\$7) same (develop\$4 or		
		rins\$3) same (spin\$4 or rotat\$3 or turn\$3)		1
	1	near5 (velocit\$3 or speed\$3)) and		
		(develop\$4 or rins\$3 or clean\$3 or dry\$3		
		or spin\$4 or rotat\$3 or turn\$3) same		
		(exhaust\$3 or air or gas or sweep\$ or		
		flow\$3 or pass\$3) near5 (velocit\$3 or	! 	
		speed\$3))		
_	825	(((resist or photoresist or	USPAT;	2003/06/20 17:15
	023	photopolymer\$7) same (develop\$4 or rins\$3	US-PGPUB;	1
		or clean\$3 or remov\$3 or residue or	EPO; JPO;	
	ĺ	rubbish or debris) same (spin\$4 or spun or	IBM TDB	
		rotat\$3 or turn\$3) near5 (velocit\$3 or	_	
		speed\$3)) not ((((semiconduct\$3 or silicon		
		or "Si" or wafer) same ((defect\$3 or		
		residue) and (resist or photoresist or		
		photopolymer\$7) and develop\$4)) and		
		(resist or photoresist or photopolymer\$7)		
		same (develop\$4 or rins\$3) same (spin\$4 or		
		same (develops4 of fills55) same (spint4 of		
		rotat\$3 or turn\$3) near5 (velocit\$3 or		
		speed\$3)) and (develop\$4 or rins\$3 or		
		clean\$3 or dry\$3 or spin\$4 or rotat\$3 or		
		turn\$3) same (exhaust\$3 or air or gas or		
		sweep\$ or flow\$3 or pass\$3) near5		
		(velocit\$3 or speed\$3))) and	ļ	
		(semiconduct\$3 or wafer or silicon or		
		"Si")		
-	320	((((resist or photoresist or	USPAT;	2003/06/20 17:18
		photopolymer\$7) same (develop\$4 or rins\$3	US-PGPUB;	·
		or clean\$3 or remov\$3 or residue or	EPO; JPO;	
		rubbish or debris) same (spin\$4 or spun or	IBM_TDB	
		rotat\$3 or turn\$3) near5 (velocit\$3 or		
		speed\$3)) not ((((semiconduct\$3 or silicon		
-	ļ	or "Si" or wafer) same ((defect\$3 or		
		residue) and (resist or photoresist or		
		photopolymer\$7) and develop\$4)) and		
		(resist or photoresist or photopolymer\$7)		
		same (develop\$4 or rins\$3) same (spin\$4 or		
		rotat\$3 or turn\$3) near5 (velocit\$3 or		
		speed\$3)) and (develop\$4 or rins\$3 or		
1		clean\$3 or dry\$3 or spin\$4 or rotat\$3 or		
		turn\$3) same (exhaust\$3 or air or gas or		
		sweep\$ or flow\$3 or pass\$3) near5		
		(velocit\$3 or speed\$3))) and		
		(semiconduct\$3 or wafer or silicon or		1
		"Si")) and (spin\$4 or spun or rotat\$3 or		}
1		turn\$3) same (exhaust\$3 or air or sweep\$3		
		or swept or inert or gas\$4)		
1 .	1	or swell or merc or dashal	1	<u>. l</u>

39	(((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not ((((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photopesist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/01/08 19:50
1	turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3))) and (semiconduct\$3 or wafer or silicon or "Si")) and (spin\$4 or spun or rotat\$3 or turn\$3) same (exhaust\$3 or air or sweep\$3 or swept or inert or gas\$4)) and (resist or photoresist or photopolym\$7) same (prim\$3 or pre adj treat\$3 or pretreat\$3) ("4556785").PN.	USPAT; US-PGPUB	2003/06/21 16:17
443	((resist or photoresist or photopolymer\$7) and (semiconduct\$3 or silicon or "Si" or wafer or substrate) same (HMDS or hexamethyldisilazane or hexamethyl adj disilazane) same (prim\$3 or pretreat\$4 or pre adj treat\$4)) not ((semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/21 19:53
237	(((resist or photoresist or photopolymer\$7) and (semiconduct\$3 or silicon or "Si" or wafer or substrate) same (HMDS or hexamethyldisilazane or hexamethyl adj disilazane) same (prim\$3 or pretreat\$4 or pre adj treat\$4)) not ((semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3)) and ((HMDS or hexamethyldisilazane or hexamethyl adj disilazane) or hexamethyl adj disilazane or silazane) or	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/21 20:06
85	prim\$3) same (seconds or "sec") (((resist or photoresist or photopolymer\$7) and (semiconduct\$3 or silicon or "Si" or wafer or substrate) same (HMDS or hexamethyldisilazane or hexamethyl adj disilazane) same (prim\$3 or pretreat\$4 or pre adj treat\$4)) not ((semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3)) and (((HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) or prim\$3) near5 vapor) same (seconds or "sec")	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/01/08 19:53

- 6097	((resist or photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not (((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3) or clean\$3 or dry\$3	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/23 16:57
- 721	or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3))) and (semiconduct\$3 or wafer or silicon or "Si")) and (spin\$4 or spun or rotat\$3 or turn\$3) same (exhaust\$3 or air or sweep\$3 or swept or inert or gas\$4)) and (resist or photoresist or photopolym\$7) same (prim\$3 or pre adj treat\$3 or pretreat\$3)) 430/311,326-327,329.ccls. and (((resist or photoresist or photoresist or photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not ((((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4) and (resist or photoresist or photopolymer\$7) and (develop\$4)) and (resist or photoresist or photopolymer\$7) and (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3)) and (semiconduct\$3 or wafer or spilicon or "Si")) and (semiconduct\$3 or wafer or speed\$3)) and (semiconduct\$3 or wafer or speed\$3)) and (semiconduct\$3 or wafer or speed\$3)) and (semiconduct\$3 or spun or rotat\$3 or turn\$3) same (exhaust\$3 or air or sweep\$3 or sweep\$ or flow\$3 or speed\$3)) and (semiconduct\$3 or wafer or speed\$3)) and (semiconduct\$3 or wafer or speed\$3)) and (semiconduct\$3 or wafer or speed\$3) or sweep\$3 or sweep\$	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/23 16:56

		[//20/211 206 207 200 gala and ///magist	исрат.	2004/01/09 20.04
-	141	(430/311,326-327,329.ccls. and (((resist	USPAT;	2004/01/08 20:04
		or photoresist or photopolymer\$7) same	US-PGPUB;	
		((develop\$4) and (rins\$3 or wash\$3 or	EPO; JPO;	
		clean\$3 or remov\$3 or residue or rubbish	IBM_TDB	
		or debris)) same (spin\$4 or spun or		
		rotat\$3 or turn\$3))		
		photoresist or photopolymer\$7) same		
		(develop\$4 or rins\$3 or clean\$3 or remov\$3		
		or residue or rubbish or debris) same		
		(spin\$4 or spun or rotat\$3 or turn\$3)		
		near5 (velocit\$3 or speed\$3)) not		
		((((semiconduct\$3 or silicon or "Si" or		
		wafer) same ((defect\$3 or residue) and		
		(resist or photoresist or photopolymer\$7)		
		and develop\$4)) and (resist or photoresist		i
		or photopolymer\$7) same (develop\$4 or		
		rins\$3) same (spin\$4 or rotat\$3 or turn\$3)		
		near5 (velocit\$3 or speed\$3)) and		
		•		
		(develop\$4 or rins\$3 or clean\$3 or dry\$3		
		or spin\$4 or rotat\$3 or turn\$3) same		
		(exhaust\$3 or air or gas or sweep\$ or		
		flow\$3 or pass\$3) near5 (velocit\$3 or		
		speed\$3))) and (semiconduct\$3 or wafer or		
		silicon or "Si")) and (spin\$4 or spun or		
		rotat\$3 or turn\$3) same (exhaust\$3 or air		
		or sweep\$3 or swept or inert or gas\$4))		
		and (resist or photoresist or		
		photopolym\$7) same (prim\$3 or pre adj		
		treat\$3 or pretreat\$3)))) and (rins\$3 or		
		wash\$3 or clean\$3 or remov\$3 or residue or		
		rubbish or debris) same (revolution or		
		"rpm")		
	10	(semiconduct\$3 same (defect\$3 and (resist	USPAT;	2004/01/08 20:11
_	10	or photoresist or photopolymer\$7) and	US-PGPUB;	2004/01/00 20:11
			1	
		develop\$4)) and (HMDS or	EPO; JPO;	
		hexamethyldisilazane or hexamethyl adj	IBM_TDB	
		disilazane or silazane) same prim\$3	HODAE	2004/01/02 02 12
-	11	(((semiconduct\$3 or silicon or "Si" or	USPAT;	2004/01/08 20:12
		wafer) same ((defect\$3 or residue) and	US-PGPUB;	
		(resist or photoresist or photopolymer\$7)	EPO; JPO;	
		and develop\$4)) and (resist or photoresist	IBM_TDB	
		or photopolymer\$7) same (develop\$4 or		
		rins\$3) same (spin\$4 or rotat\$3 or turn\$3)		
		near5 (velocit\$3 or speed\$3)) and		
		(develop\$4 or rins\$3 or clean\$3 or dry\$3		
		or spin\$4 or rotat\$3 or turn\$3) same		
1		(exhaust\$3 or air or gas or sweep\$ or		
		flow\$3 or pass\$3) near5 (velocit\$3 or		
		speed\$3)		
L	·	ppccays/		

	.,			
_	40	(((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3	USPAT; US-PGPUB;	2003/10/15 15:35
		or clean\$3 or remov\$3 or residue or	EPO; JPO;	
		rubbish or debris) same (spin\$4 or spun or	IBM TDB	•
		rotat\$3 or turn\$3) near5 (velocit\$3 or	_	
		speed\$3)) not ((((semiconduct\$3 or silicon		
		or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or		
		photopolymer\$7) and develop\$4)) and		
		(resist or photoresist or photopolymer\$7)		
		same (develop\$4 or rins\$3) same (spin\$4 or		
		rotat\$3 or turn\$3) near5 (velocit\$3 or		
		speed\$3)) and (develop\$4 or rins\$3 or		
		clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or		
		sweep\$ or flow\$3 or pass\$3) near5		
		(velocit\$3 or speed\$3))) and		
		(semiconduct\$3 or wafer or silicon or		
		"Si")) and (spin\$4 or spun or rotat\$3 or		
		turn\$3) same (exhaust\$3 or air or sweep\$3		
		or swept or inert or gas\$4)) and (resist		
		or photoresist or photopolym\$7) same (prim\$3 or pre adj treat\$3 or pretreat\$3)		
_	86	(((resist or photoresist or	USPAT;	2003/10/15 15:37
		photopolymer\$7) and (semiconduct\$3 or	US-PGPUB;	2000/10/10 10:07
		silicon or "Si" or wafer or substrate)	EPO; JPO;	
		same (HMDS or hexamethyldisilazane or	IBM_TDB	
		hexamethyl adj disilazane) same (prim\$3 or		
		pretreat\$4 or pre adj treat\$4)) not ((semiconduct\$3 same (defect\$3 and (resist		
		or photoresist or photopolymer\$7) and		
		develop\$4)) and (HMDS or		
		hexamethyldisilazane or hexamethyl adj		
		disilazane or silazane) same prim\$3)) and		
		(((HMDS or hexamethyldisilazane or		
		hexamethyl adj disilazane or silazane) or		
		prim\$3) near5 vapor) same (seconds or "sec")		
_	148	(430/311,326-327,329.ccls. and (((resist	USPAT;	2003/10/15 15:55
		or photoresist or photopolymer\$7) same	US-PGPUB;	2000, 10, 10 10.00
		((develop\$4) and (rins\$3 or wash\$3 or	EPO; JPO;	
		clean\$3 or remov\$3 or residue or rubbish	IBM_TDB	
		or debris)) same (spin\$4 or spun or		
		rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same		
		(develop\$4 or rins\$3 or clean\$3 or remov\$3		
		or residue or rubbish or debris) same		
		(spin\$4 or spun or rotat\$3 or turn\$3)		
		near5 (velocit\$3 or speed\$3)) not		
		((((semiconduct\$3 or silicon or "Si" or		
		wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7)		
		and develop\$4)) and (resist or photoresist		
		or photopolymer\$7) same (develop\$4 or		
		rins\$3) same (spin\$4 or rotat\$3 or turn\$3)		
		near5 (velocit\$3 or speed\$3)) and		
		(develop\$4 or rins\$3 or clean\$3 or dry\$3		
		or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or		
		flow\$3 or pass\$3) near5 (velocit\$3 or		
		speed\$3))) and (semiconduct\$3 or wafer or		
		silicon or "Si")) and (spin\$4 or spun or		
		rotat\$3 or turn\$3) same (exhaust\$3 or air		
	i	or sweep\$3 or swept or inert or gas\$4))		
		<pre>and (resist or photoresist or photopolym\$7) same (prim\$3 or pre adj</pre>		i
		treat\$3 or pretreat\$3)))) and (rins\$3 or		
		wash\$3 or clean\$3 or remov\$3 or residue or		
		rubbish or debris) same (revolution or		
1		"rpm")		